

N-channel TrenchMOS standard level FET 28 July 2016

**Product data sheet** 

### 1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	234	W
Static character	eristics				- 1		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		-	3.23	4.5	mΩ
Dynamic chara	acteristics						
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	26.1	-	nC

[1] Continuous current is limited by package.

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G LIFE
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

# 6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK764R4-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK764R4-60E	BUK764R4-60E

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	60	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	234	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	100	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	620	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
BUK764R4-60E	JK764R4-60E All information provided in this document is subject to legal disclaimers. © Nexperia B.V. 2017. All rights reserved					

# **BUK764R4-60E**

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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain	diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	620	А
Avalanche ru	Avalanche ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 100 \; A;  V_{sup} \leq 60 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 60 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ \hline Fig. \; 4 \end{array}$	[ <u>2][3]</u>	-	273	mJ

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

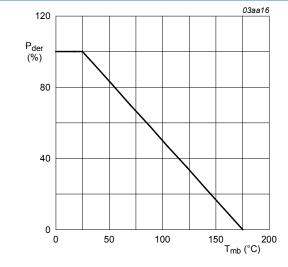
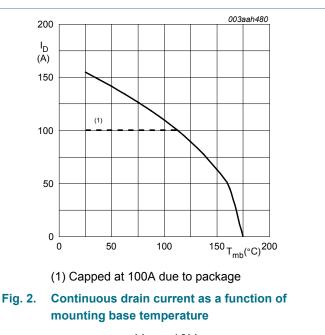


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

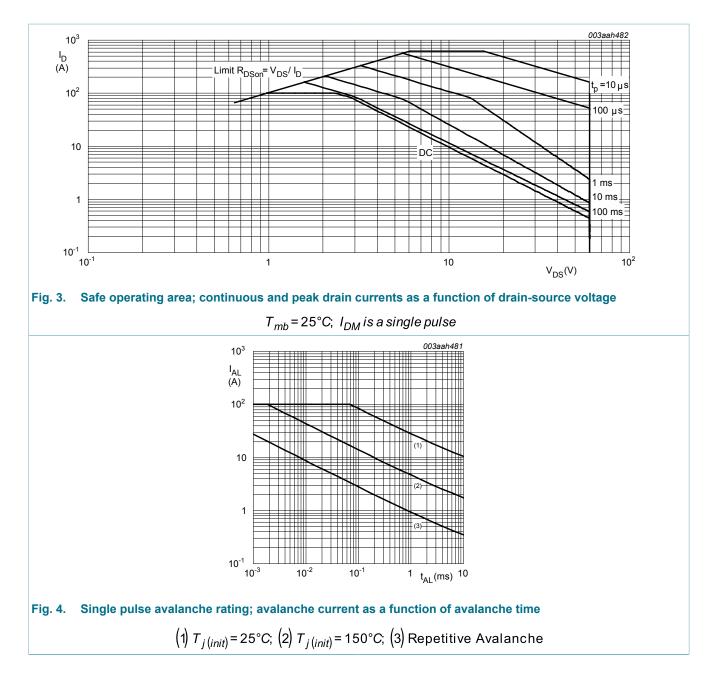
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$





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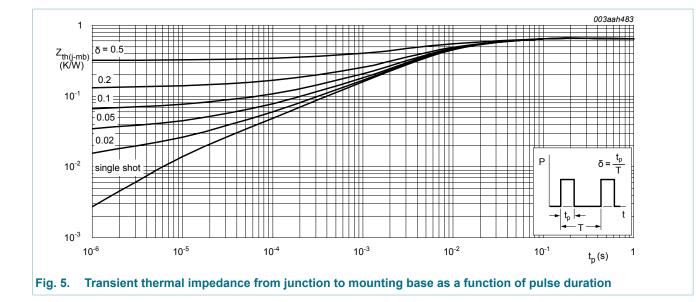
### 9. Thermal characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.64	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

#### Table 6. Thermal characteristics

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### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics	· · · ·					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V	
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	54	-	-	V	
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V		
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V		
I <sub>DSS</sub> drain leakage current	$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.08	1	μA		
		$V_{DS}$ = 60 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA	
I <sub>GSS</sub> gate leakage c	I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA	
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	-	3.23	4.5	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	9.8	mΩ	
Dynamic ch	naracteristics						
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 48 V; $V_{GS}$ = 10 V;	-	82	-	nC	
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	18.5	-	nC	
Q <sub>GD</sub>	gate-drain charge	1	-	26.1	-	nC	

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;		-	4670	6230	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	637	765	pF
C <sub>rss</sub>	reverse transfer capacitance			-	377	516	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 45 V; R <sub>L</sub> = 1.8 Ω; V <sub>GS</sub> = 10 V;		-	23	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$		-	39	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	50	-	ns
t <sub>f</sub>	fall time			-	40	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad		-	7.5	-	nH
Source-dra	in diode	1	I		I		
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.81	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI_{S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	38.2	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V		-	49.6	-	nC

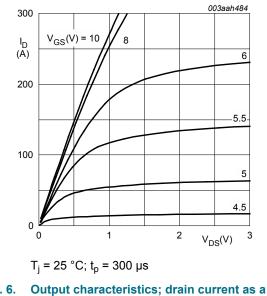
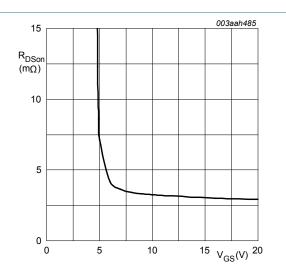


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

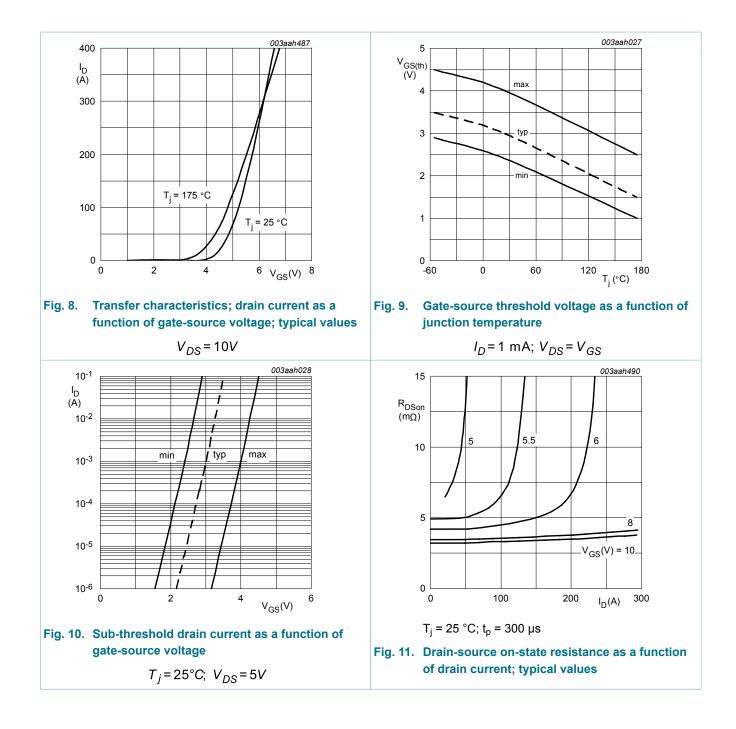




 $T_j = 25^{\circ}C; I_D = 25A$ 

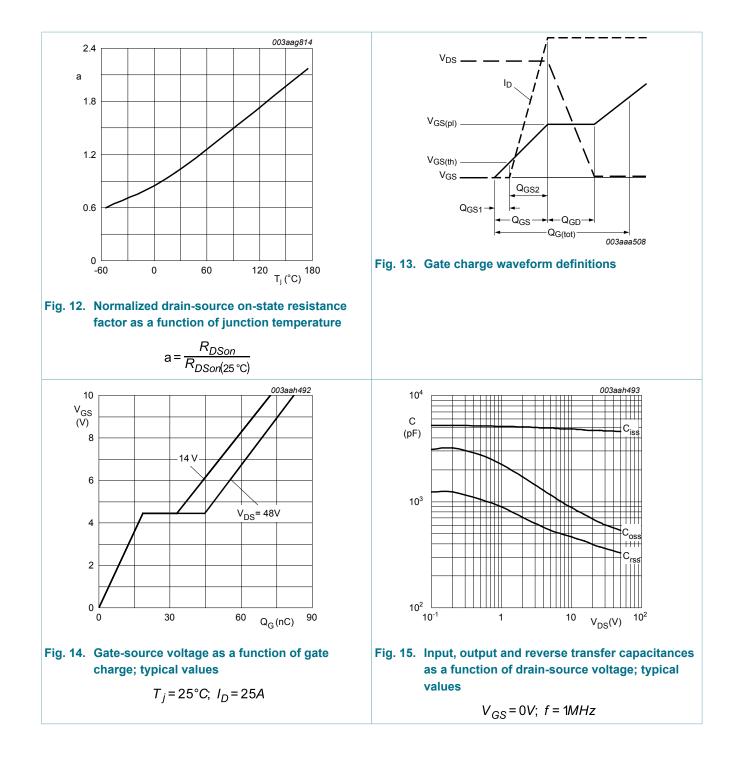
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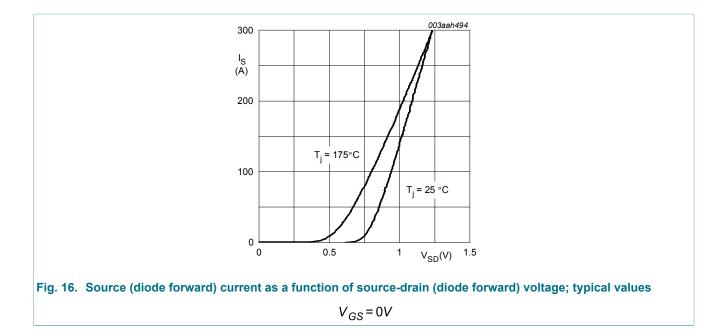
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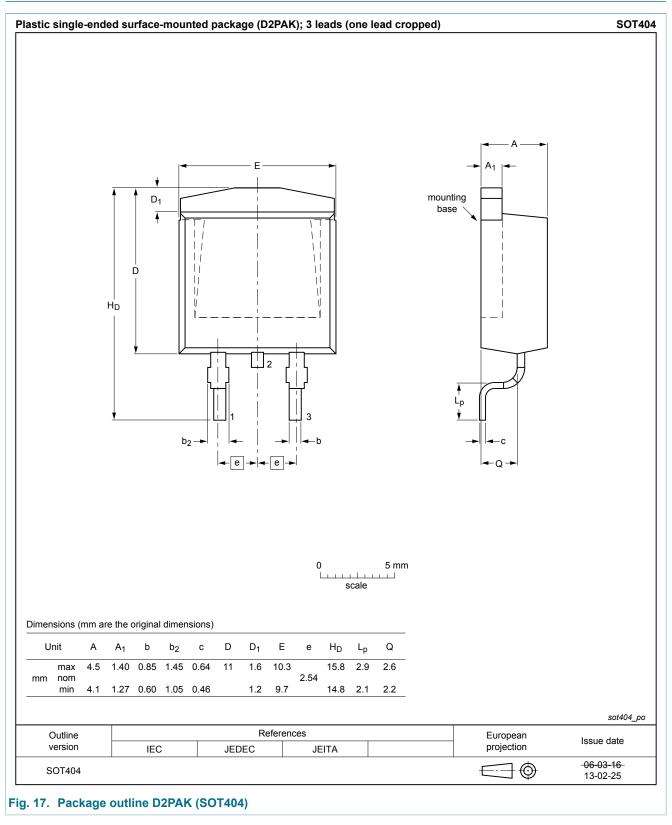
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### 11. Package outline



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### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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